## MSKSEMI















**ESD** 

TVS

TSS

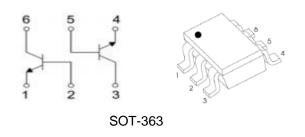
MOV

GDT

**PLED** 

# Broduct data sheet





### MMDT3052DW ( NPN+NPN) Silicon Epitaxial Planar Transistor

#### **Features**

• Each transistor elements are independent

#### **Applications**

• For low frequency amplify application

#### **MARKING: 5G**

#### Absolute Maximum Ratings ( $T_a = 25^{\circ}C$ )

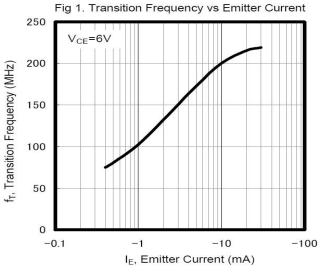
Parameter	Symbol	Value	Unit
Collector Base Voltage	V <sub>CBO</sub>	50	V
Collector Emitter Voltage	V <sub>CEO</sub>	50	V
Emitter Base Voltage	$V_{EBO}$	6	V
Collector Current	Ic	200	mA
Power Dissipation	P <sub>tot</sub>	150	mW
Junction Temperature	Tj	125	$^{\circ}$
Storage Temperature Range	T <sub>stg</sub>	- 55 to + 125	$^{\circ}$

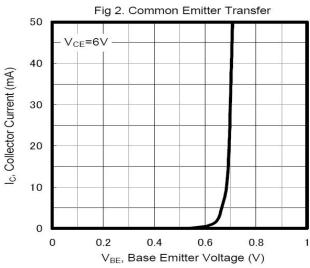
#### Characteristics at T<sub>a</sub> = 25 °C

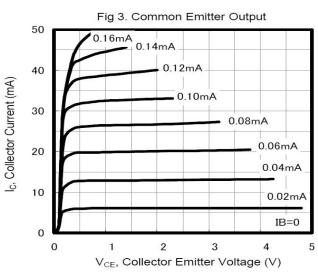
Parameter		Symbol	Min.	Тур.	Max.	Unit
, o	E F G	h <sub>FE</sub> h <sub>FE</sub> h <sub>FE</sub>	90 120 200 350	- - -	- 240 400 700	- - -
Collector Base Cutoff Current at V <sub>CB</sub> = 50 V		I <sub>CBO</sub>	-	-	100	nA
Emitter Base Cutoff Current at V <sub>EB</sub> = 6 V		I <sub>EBO</sub>	-	-	100	nA
Collector Emitter Breakdown Voltage at I <sub>C</sub> = 100 μA		V <sub>(BR)CEO</sub>	50	-	-	V
Collector Emitter Saturation Voltage at I <sub>C</sub> = 100 mA, I <sub>B</sub> = 10 mA		V <sub>CE(sat)</sub>	-	-	0.3	V
Transition Frequency at $V_{CE} = 6 \text{ V}$ , $-I_E = 10 \text{ mA}$		f <sub>T</sub>	-	200	-	MHz
Collector Output Capacitance at V <sub>CB</sub> = 6 V, f = 1 MHz		C <sub>ob</sub>	-	2.5	-	pF

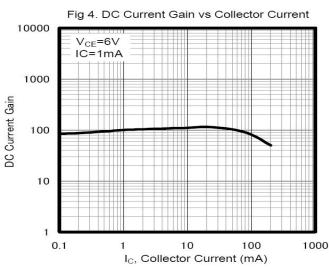


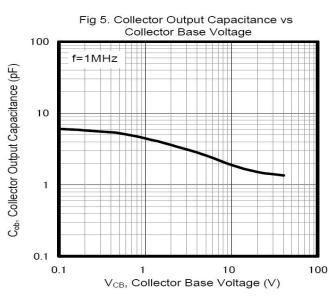
#### **Electrical Characteristics Curves**













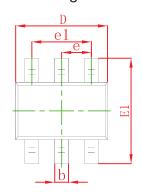


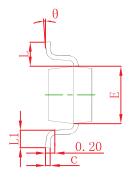
MMDT3052DW

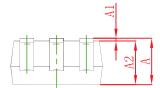




#### **SOT-363** Package Outline Dimensions

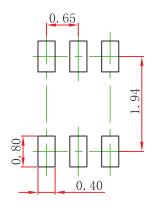






Symbol	Dimensions In Millimeters		Dimension	ns In Inches	
Symbol	Min	Max	Min	Max	
Α	0.900	1.100	0.035	0.043	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.000	0.035	0.039	
b	0.150	0.350	0.006	0.014	
С	0.100	0.150	0.004	0.006	
D	2.000	2.200	0.079	0.087	
E	1.150	1.350	0.045	0.053	
E1	2.150	2.400	0.085	0.094	
е	0.650	) TYP	0.026	S TYP	
e1	1.200	1.400	0.047	0.055	
L	0.525 REF		0.021 REF		
L1	0.260	0.460	0.010	0.018	
θ	0°	8°	0°	8°	

#### SOT-363 Suggested Pad Layout



#### Note:

- 1.Controlling dimension:in millimeters. 2.General tolerance:± 0.05mm.
- 3. The pad layout is for reference purposes only.

#### **REEL SPECIFICATION**

P/N	PKG	QTY
MMDT3052DW	SOT-363	3000



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